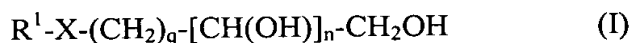


AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising a compound having a structure in which each of two or more adjacent carbon atoms has a hydroxyl group in a molecule, and water, wherein the compound having a structure in which each of two or more adjacent carbon atoms has a hydroxyl group in a molecule is represented by the formula (I):



wherein R^1 is a hydrocarbon group having 1 to 24 carbon atoms; X is a group represented by $(CH_2)_m$, wherein m is 1, oxygen atom, sulfur atom, COO group, OCO group, a group represented by NR^2 or $O(R^2O)P(O)O$, wherein R^2 is hydrogen atom or a hydrocarbon group having 1 to 24 carbon atoms; q is 0 or 1; and n is an integer of 1 to 4.

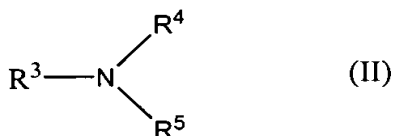
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Claim 2 (Original): The polishing liquid composition according to claim 1, further comprising an organic acid.

Claim 3 (Original): The polishing liquid composition according to claim 2, wherein the organic acid is an etching agent.

Claim 4 (Original): The polishing liquid composition according to claim 1, further comprising an etching agent comprising an inorganic acid.

Claim 5 (Original): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising an aliphatic carboxylic acid having 7 to 24 carbon atoms and/or a salt thereof, an etching agent comprising an organic acid, and water.

Claim 6 (Original): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising an amine compound represented by the following general formula (II):



wherein R³ is a linear or branched alkyl group having 4 to 18 carbon atoms, a linear or branched alkenyl group having 4 to 18 carbon atoms, an aryl group having 6 to 18 carbon atoms, and an aralkyl group having 7 to 18 carbon atoms; each of R⁴ and R⁵, which may be identical or different, is hydrogen atom, a linear alkyl group having 1 to 8 carbon atoms or a branched alkyl group having 3 to 8 carbon atoms, or a group represented by H-(OR⁶)_z-, wherein R⁶ is a linear alkylene group having 1 to 3 carbon atoms, or a branched alkylene group having 3 carbon atoms; and Z is a number of 1 to 20, and/or a salt thereof, an etching agent, an oxidizing agent, and water.

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Claim 7 (Previously Amended): The polishing liquid composition according to Claim 1, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 8 (Cancelled).

Claim 9 (Previously Amended): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of Claim 1, thereby smoothening the semiconductor substrate.

Claim 10 (Previously Amended): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of Claim 1, thereby smoothening the semiconductor substrate.

Claim 11 (New): The polishing liquid composition according to claim 2, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 12 (New): The polishing liquid composition according to claim 5, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 13 (New): The polishing liquid composition according to claim 6, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 14 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 2, thereby smoothening the semiconductor substrate.

Claim 15 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 5, thereby smoothening the semiconductor substrate.

Claim 16 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 6, thereby smoothening the semiconductor substrate.

Claim 17 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 7, thereby smoothening the semiconductor substrate.

Claim 18 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a

metal layer using the polishing liquid composition of claim 11, thereby smoothening the semiconductor substrate.

Claim 19 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 12, thereby smoothening the semiconductor substrate.

Claim 20 (New): A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 13, thereby smoothening the semiconductor substrate.

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Claim 21 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 2, thereby smoothening the semiconductor substrate.

Claim 22 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 5, thereby smoothening the semiconductor substrate.

Claim 23 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 5, thereby smoothening the semiconductor substrate.

Claim 24 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a

metal layer using the polishing liquid composition of claim 7, thereby smoothening the semiconductor substrate.

Claim 25 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 11, thereby smoothening the semiconductor substrate.

b' Claim 26 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 12, thereby smoothening the semiconductor substrate.

Claim 27 (New): A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising as insulating layer and a metal layer using the polishing liquid composition of claim 13, thereby smoothening the semiconductor substrate.

SUPPORT FOR NEW CLAIMS

New Claims 11-27 are supported by the claims as originally filed and throughout the specification. No new matter is believed to be added by entry of new Claims 11-27. Claims 1-7 and 9-27 are active.